

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - ambient	R_{thJA}	minimal footprint	-	-	250	K/W
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Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified
Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=-10\text{ V}$, $I_D=250\text{ }\mu\text{A}$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=3\text{ V}$, $I_D=50\text{ }\mu\text{A}$	-2.9	-2.2	-1.8	
Drain-source cutoff current	$I_{D(off)}$	$V_{DS}=100\text{ V}$, $V_{GS}=-10\text{ V}$, $T_j=25\text{ °C}$	-	-	0.1	μA
		$V_{DS}=100\text{ V}$, $V_{GS}=-10\text{ V}$, $T_j=125\text{ °C}$	-	-	10	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$	-	-	10	nA
On-state drain current	I_{DSS}	$V_{GS}=0\text{ V}$, $V_{DS}=10\text{ V}$	90	-	-	mA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=0\text{ V}$, $I_D=0.05\text{ A}$	-	5.3	12	Ω
		$V_{GS}=10\text{ V}$, $I_D=0.19\text{ A}$	-	2.9		
Transconductance	g_{fs}	$ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=0.15\text{ A}$		0.20	-	S

Threshold voltage $V_{GS(th)}$ sorted in bands²⁾

J	$V_{GS(th)}$	$V_{DS}=3\text{ V}$, $I_D=50\text{ }\mu\text{A}$	-2	-	-1.8	V
K			-2.15	-	-1.95	
L			-2.3	-	-2.1	
M			-2.45	-	-2.25	
N			-2.6	-	-2.4	

²⁾ Each reel contains transistors out of one band whose identifying letter is printed on the reel label. A specific band cannot be ordered separately.

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			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS} = -10\text{ V}, V_{DS} = 25\text{ V},$ $f = 1\text{ MHz}$	-	51	68	pF
Output capacitance	C_{oss}		-	9	13	
Reverse transfer capacitance	C_{rss}		-	4	7	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50\text{ V},$ $V_{GS} = -3 \dots -7\text{ V},$ $I_D = 0.12\text{ A}, R_{G,ext} = 6\text{ }\Omega$	-	2.9	4.2	ns
Rise time	t_r		-	2.7	4.0	
Turn-off delay time	$t_{d(off)}$		-	11	17	
Fall time	t_f		-	27	40	

Gate Charge Characteristics

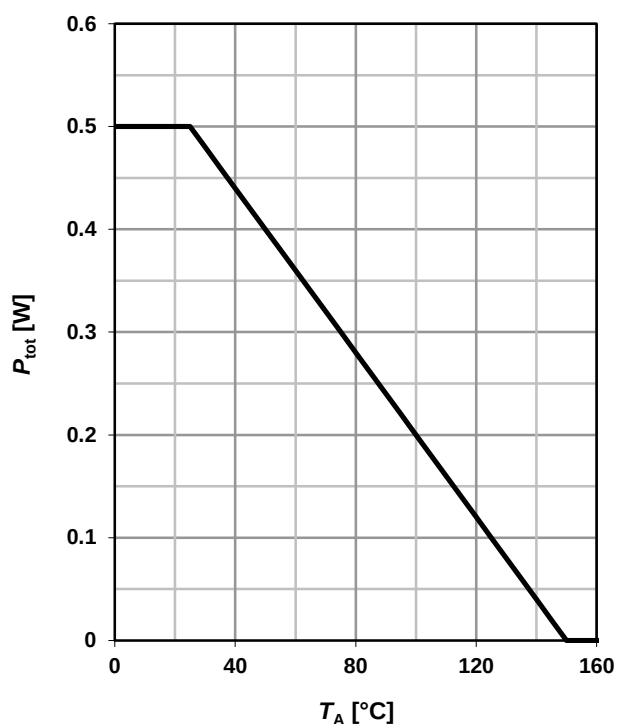
Gate to source charge	Q_{gs}	$V_{DD} = 80\text{ V}, I_D = 0.12\text{ A},$ $V_{GS} = -3\text{ to }7\text{ V}$	-	0.12	0.16	nC
Gate to drain charge	Q_{gd}		-	0.9	1.4	
Gate charge total	Q_g		-	2.1	2.8	
Gate plateau voltage	$V_{plateau}$		-	-0.43	-	V

Reverse Diode

Diode continuous forward current	I_S	$T_A = 25\text{ }^\circ\text{C}$	-	-	0.19	A
Diode pulse current	$I_{S,pulse}$		-	-	0.76	
Diode forward voltage	V_{SD}	$V_{GS} = -10\text{ V}, I_F = 0.19\text{ A},$ $T_j = 25\text{ }^\circ\text{C}$	-	0.82	1.2	V
Reverse recovery time	t_{rr}	$V_R = 50\text{ V}, I_F = 0.12\text{ A},$ $di_F/dt = 100\text{ A}/\mu\text{s}$	-	20.5	25.6	ns
Reverse recovery charge	Q_{rr}		-	9.7	12.1	nC

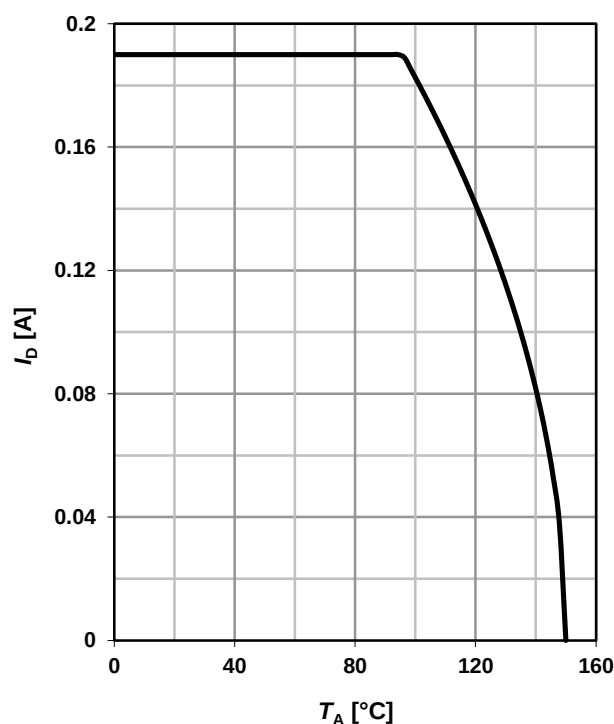
1 Power dissipation

$$P_{\text{tot}} = f(T_A)$$



2 Drain current

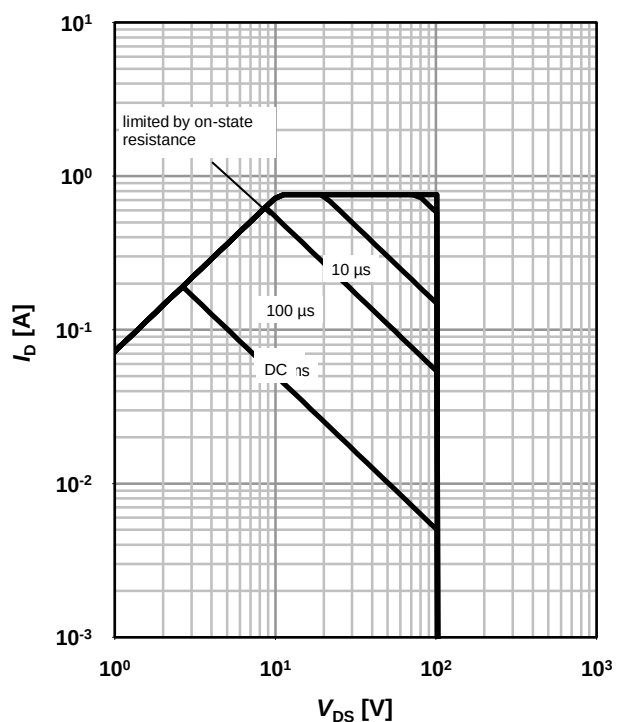
$$I_D = f(T_A); V_{GS} \geq 10 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{DS}); T_A = 25 \text{ °C}; D = 0$$

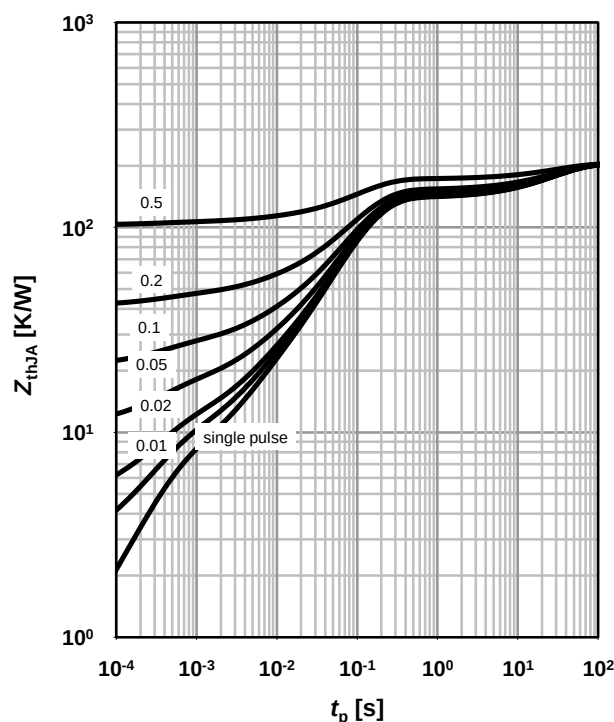
parameter: t_p



4 Max. transient thermal impedance

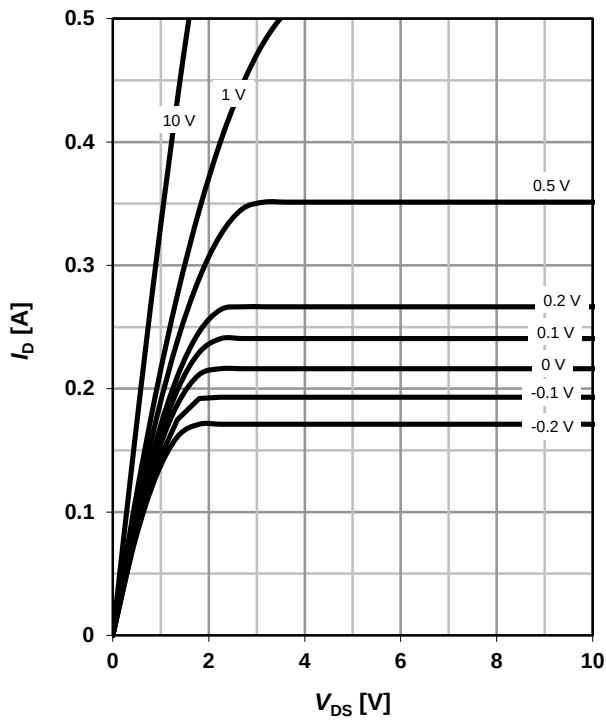
$$Z_{\text{thJA}} = f(t_p)$$

parameter: $D = t_p/T$



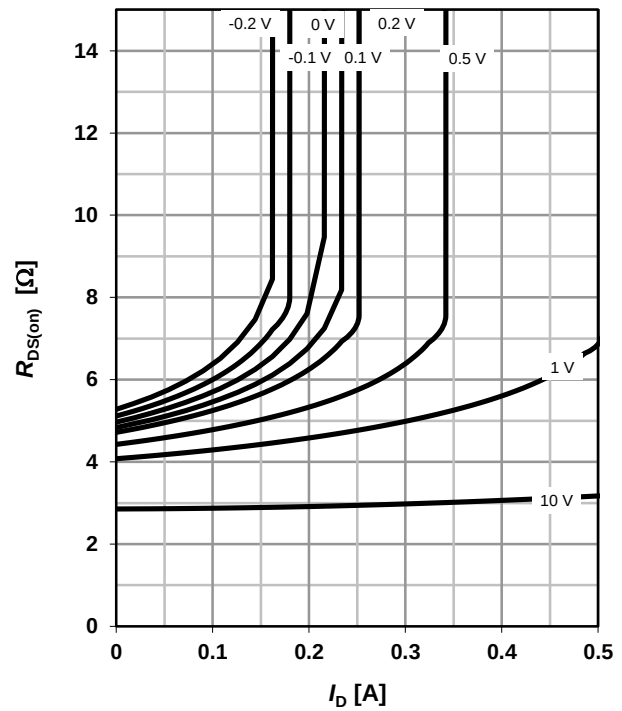
5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

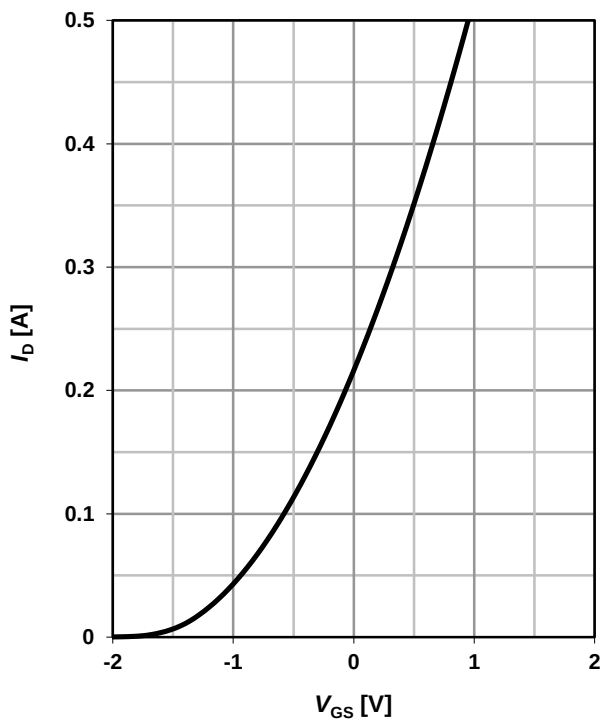
parameter: V_{GS}


6 Typ. drain-source on resistance

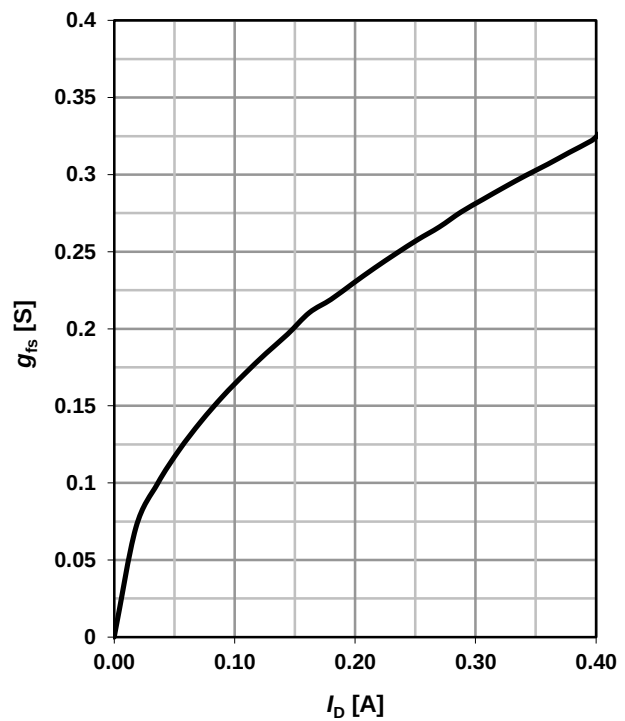
 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$

parameter: V_{GS}


7 Typ. transfer characteristics

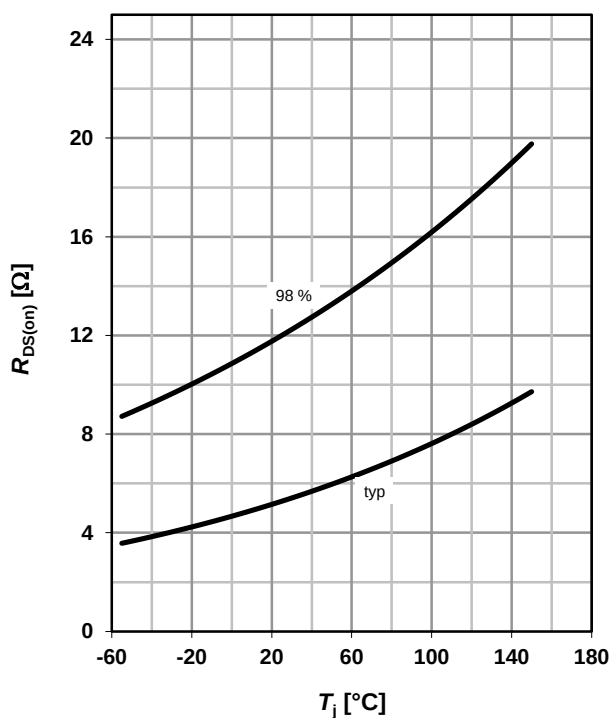
 $I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$


8 Typ. forward transconductance

 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$


9 Drain-source on-state resistance

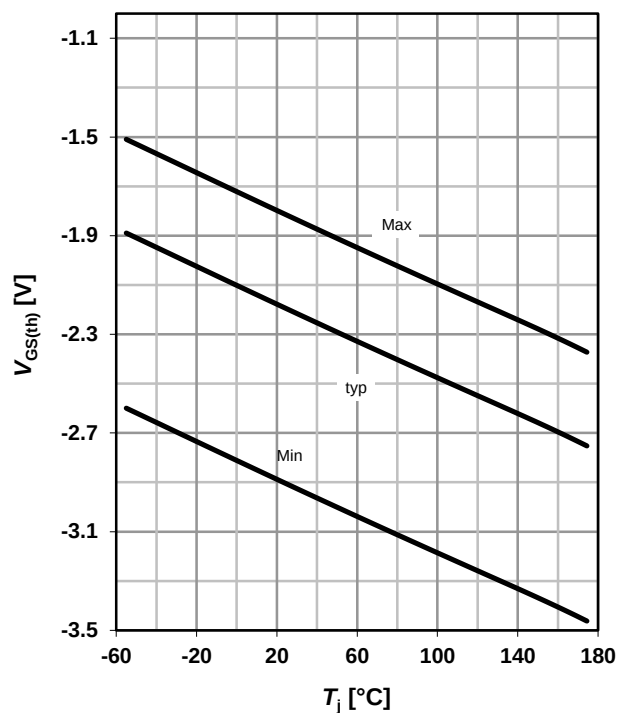
$$R_{DS(on)} = f(T_j); I_D = 0.05 \text{ A}; V_{GS} = 0 \text{ V}$$



10 Typ. gate threshold voltage

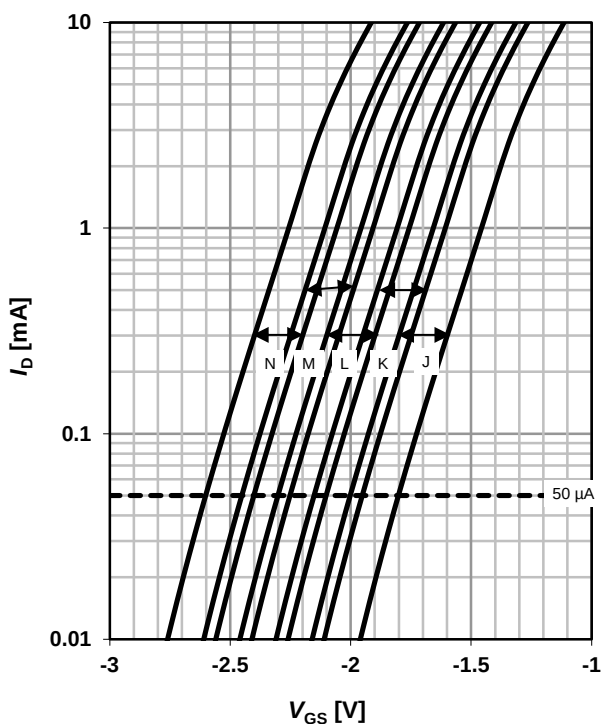
$$V_{GS(th)} = f(T_j); V_{DS} = 3 \text{ V}; I_D = 50 \text{ μA}$$

parameter: I_D



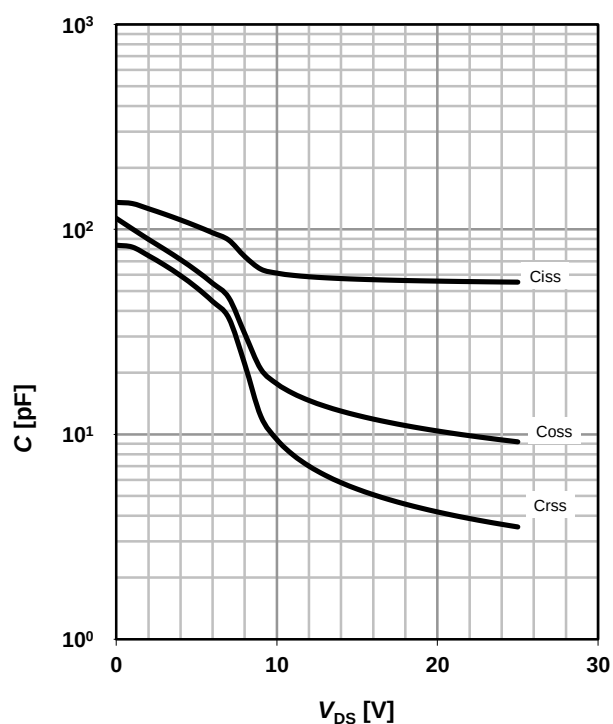
11 Threshold voltage bands

$$I_D = f(V_{GS}); V_{DS} = 3 \text{ V}; T_j = 25 \text{ °C}$$



12 Typ. capacitances

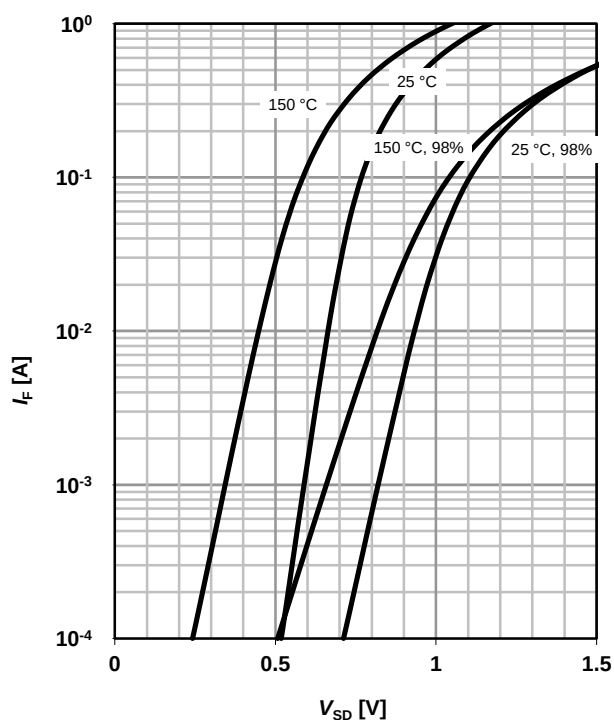
$$C = f(V_{DS}); V_{GS} = -10 \text{ V}; f = 1 \text{ MHz}$$



13 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

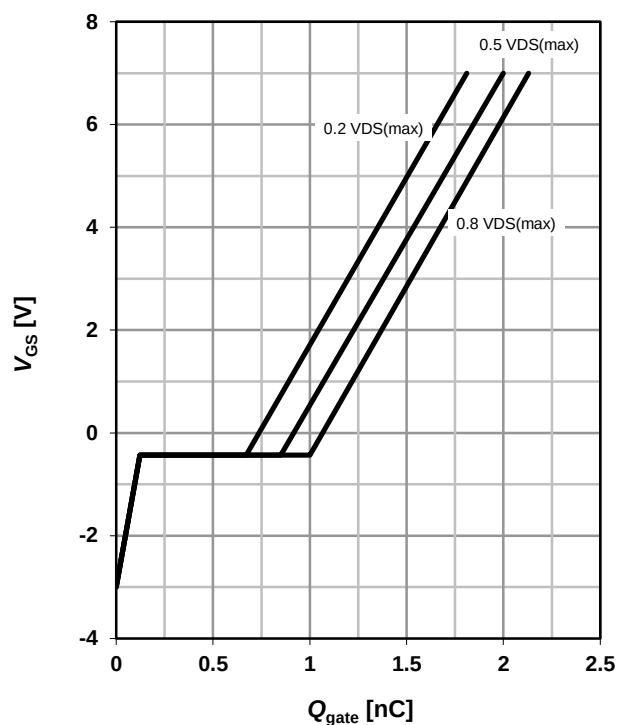
parameter: T_j



15 Typ. gate charge

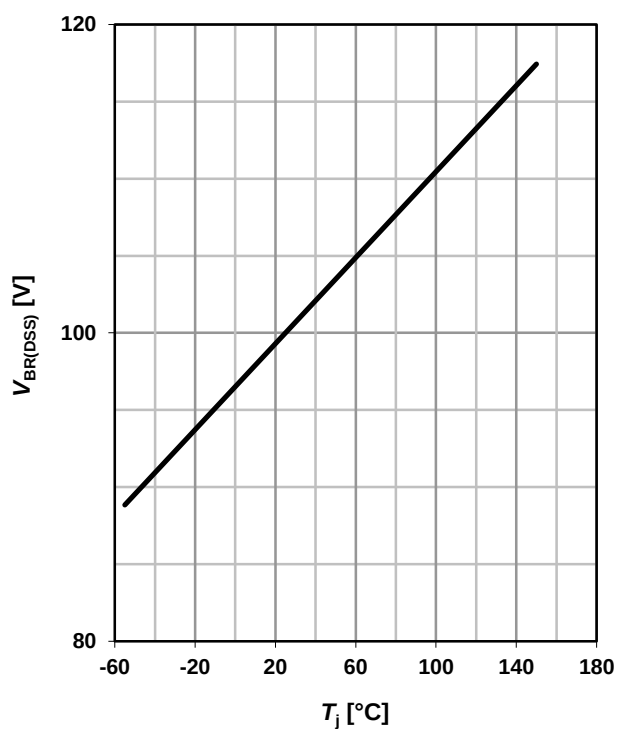
$$V_{GS} = f(Q_{gate}); I_D = 0.12 \text{ A pulsed}$$

parameter: V_{DD}

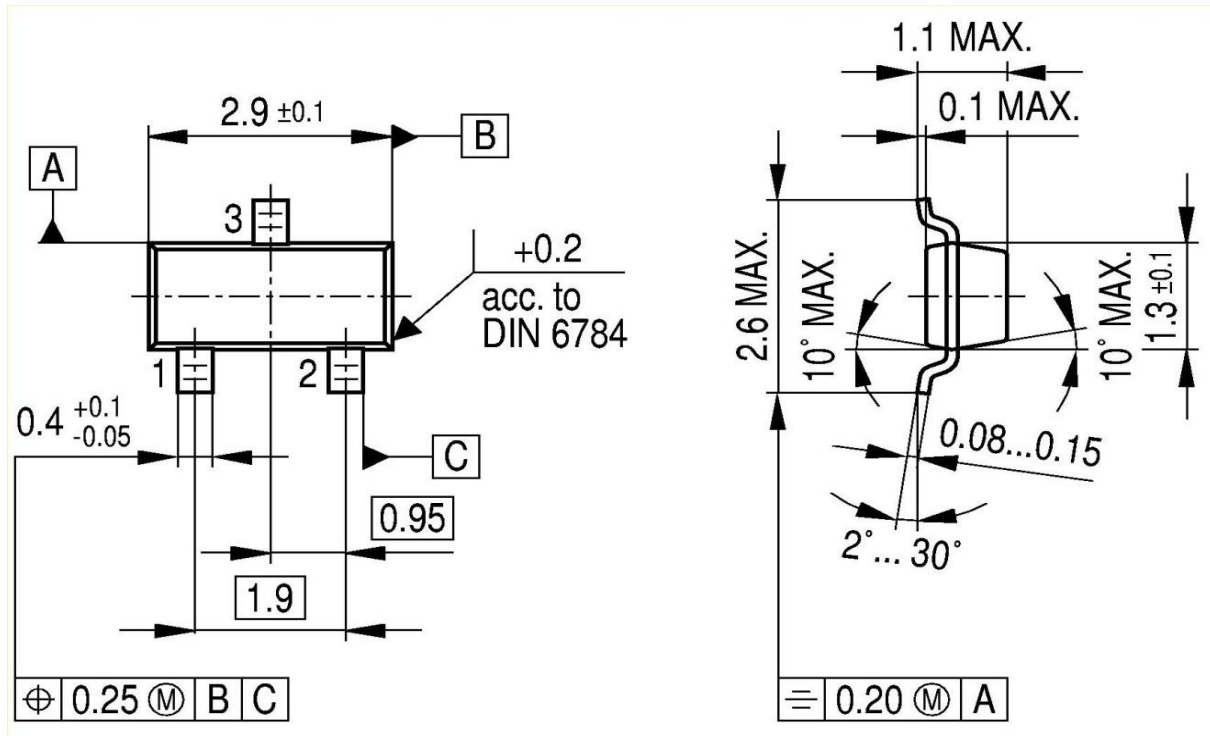


16 Drain-source breakdown voltage

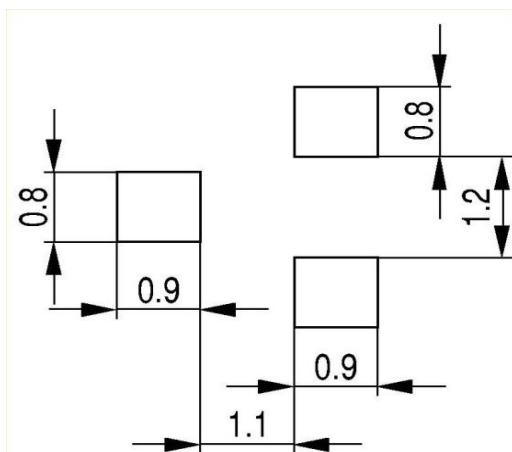
$$V_{BR(DSS)} = f(T_j); I_D = 250 \text{ } \mu\text{A}$$



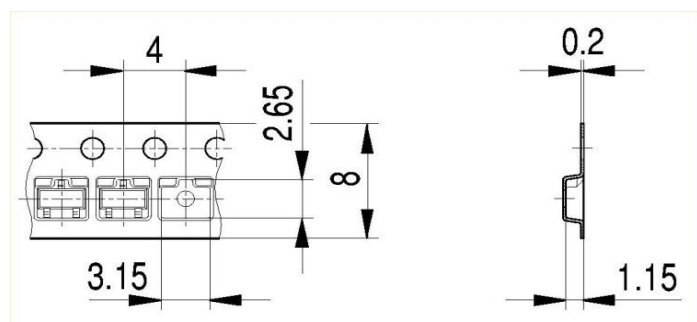
Package Outline:



Footprint:



Packaging:



Dimensions in mm

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